

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2001-352748

(43)Date of publication of application : 21.12.2001

(51)Int.Cl.

H02M 1/08

H03K 17/08

H03K 17/56

(21)Application number : 2000-167415

(71)Applicant : DENSO CORP

(22)Date of filing : 05.06.2000

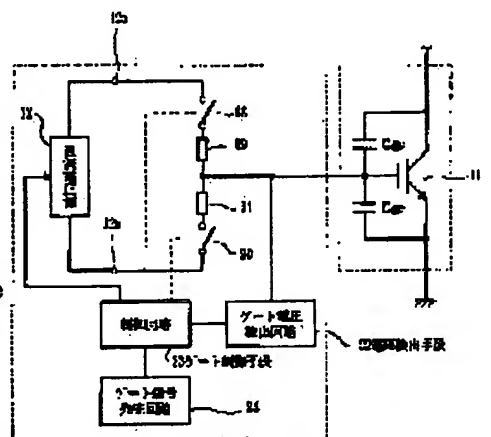
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## (54) GATE DRIVE CIRCUIT FOR SEMICONDUCTOR SWITCHING ELEMENT

## (57)Abstract:

PROBLEM TO BE SOLVED: To reduce a switching loss while suppressing occurrence of a current surge and a noise at a turning on time of an insulated gate type semiconductor switching element and to prolong a lifetime of the element.

SOLUTION: A control circuit 23 turns on a switching element 18 for turning on an IGBT 11 when the IGBT 11 is turned on based on a gate timing signal from a gate signal generator 24, outputs an on-voltage from a first output terminal 12a of a DC voltage source 12, lowers a level of the on-voltage from the first output terminal 12a thereafter when the gate voltage of the IGBT 11 for detecting a gate voltage detector 22 arrives at a first set value and further resets the level of the on-voltage to an original state when the gate voltage to be detected by the gate voltage detector 22 arrives at a second set value (> the first set value).



12: 絶縁ゲート型半導体  
スイッチング素子  
18: クーリング用スイッチング素子  
22: オンオフスイッチング素子

## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]